According to International Patent Classification (IPC) or to both national classification and IPC

 $\label{lem:minimum} \begin{array}{ll} \mbox{Minimum documentation searched (classification system followed by classification symbols)} \\ \mbox{IPC 7} & \mbox{H01L} \end{array}$

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

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X	MATSUNAGA Y ET AL: "Effect of surface treatment during Ge<+>/B<+> two step ion implantation" ION IMPLANTATION TECHNOLOGY PROCEEDINGS, 1998 INTERNATIONAL CONFERENCE ON KYOTO, JAPAN 22-26 JUNE 1998, PISCATAWAY, NJ, USA, IEEE, US, vol. 1, 22 June 1998 (1998-06-22), pages 668-671, XP010362035 ISBN: 0-7803-4538-X the whole document	1-10	
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Patent family members are listed in annex.
 "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art. "8" document member of the same patent family
Date of mailing of the international search report
27/07/2005
Authorized officer Wolff, G

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